

CLAIMS:

1. A method of manufacturing a semiconductor device comprising the steps of:

5 forming a semiconductor film comprising silicon in contact with a silicon nitride film;

forming a continuous layer of a material including a catalyst capable of promoting a crystallization of silicon onto at least a portion of said semiconductor film;

10 heating said semiconductor film in order to crystallize said semiconductor film; and then

irradiating said semiconductor film with light in order to improve the crystallinity of said semiconductor film.

add B2

add S1

Add F1

add F2

add F3

Add L1